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**INFORMATION DISCLOSURE
STATEMENT BY APPLICANT**

Date Submitted: August 3, 2005

(use as many sheets as necessary)

Sheet 1 of 1

Complete if Known

Application Number	10/526,745
Filing Date	03/07/2005
First Named Inventor	Katsuya HASEGAWA
Group Art Unit	Unassigned
Examiner Name	Unassigned
Attorney Docket Number	017700-0174

U.S. PATENT DOCUMENTS

Examiner Initials*	Cite No. ¹	U.S. Patent Document		Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YYYY	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number	Kind Code ² (if known)			
	A1	2004/0224851	A	KAKIMOTO et al.	11-11-2004	
	A2	6,743,533	B1	KAKIMOTO et al.	06-01-2004	
	A3	5,607,899		YOSHIDA et al.	03-04-1997	

FOREIGN PATENT DOCUMENTS

Examiner Initials*	Cite No. ¹	Foreign Patent Document			Name of Patentee or Applicant of Cited Documents	Date of Publication of Cited Document MM-DD-YYYY	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T ⁶
		Office ³	Number ⁴	Kind Code ⁵ (if known)				
	A4	JP	2000-299026		FUJIKURA LTD.	10-24-2000		A
	A5	JP	07-291626		SUMITOMO ELECTRIC IND. LTD.	11-07-1995		A

NON PATENT LITERATURE DOCUMENTS

Examiner Initials*	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.) date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ⁶
	A6	"Material Engineering for Studying with Personal Computer," The 2001 Seminar of Japan Institute of Metals, November 2001, pp. 21-31.	
	A7	K. HASEGAWA et al., "Preparation of SmBa ₂ Cu ₃ O ₇ Films With Improved In-plane Alignment by Pulsed Laser Deposition," J. Japan Inst. Metal., Vol. 66, 2002, pp. 320-328.	
	A8	M. NAKAMURA et al., "Fabrication of Single Crystal of SmBa ₂ Cu ₃ O _{7-x} by the Modified Top-Seeded Solution Growth Method in Low Oxygen Partial Pressure Atmosphere, Japan J. of Applied Phys., Vol. 34, 1995, pp. 6031-6035.	
	A9	T. MURATA et al., "Interface Structures in NdBCO/MgO and YBCO/MgO Superconducting Films Grown by LPE Method," The Fourth Pacific Rim International Conference [of] on Advanced Materials and Processing, 2001, pp. 729-732, The Japan Institute of Metals.	
	A10	K. SUDOH et al., "Superconducting properties and surface morphology of SmBa ₂ Cu ₃ O _{6.5} thin films," Physica C, Vol. 357-360, 2001, pp. 1358-1360; Elsevier Science.	
	A11	Y. WU et al., "Atomic configurations of YBa ₂ Cu ₃ O _{7-x} /MgO interfaces," Physica C 371, 2002, pp. 309-314, Elsevier Science.	
	A12	Q.D. JIANG et al., "Surface Morphology and In-Plane-Epitaxy of SmBa ₂ Cu ₃ O _{7-δ} Films on SrTiO ₃ (001) Substrates Studied by STM and Grazing Incidence X-ray Diffraction, Solid State Comm. 98:2, pp 157-161.	

ALL REFERENCES CONSIDERED EXCEPT WHERE LINED THROUGH. /K.M.V./

Examiner
Signature

/Kallambella Vijayakumar/

Date
Considered

03/25/2008

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¹ Unique citation designation number. ² See attached Kinds of U.S. Patent Documents. ³ Enter Office that issued the document, by the two-letter code (WIPO Standard ST.3). ⁴ For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the serial number of the patent document.

⁵ Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST. 16 if possible. ⁶ Applicant is to place a check mark here if English language Translation is attached.

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